Product data sheet

1. General description

Enhanced ultrafast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- · High thermal cycling performance
- Low on-state losses
- · Low thermal resistance
- Soft recovery characteristic
- Surface-mountable package

3. Applications

- Dual Mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	$\delta = 0.5$; $T_{mb} \le 115$ °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	9	A
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; SQW	-	-	18	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 3</u>	-	-	91	Α
		t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 3</u>	-	-	100	Α
Static characte	eristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.25	1.7	V
Dynamic char	acteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 6}}{}$	-	17.5	35	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection	mb	K ——— A
2	K	cathode[1]		001aaa020
3	Α	anode	Li	
mb	K	mounting base; cathode		
			D2PAK (SOT404)	

^[1] It is not possible to connect to pin 2 of the SOT404 package.

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV29FB-600	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} \leq 115 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	9	A
I _{FRM}	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_{mb} \le 115 \; ^{\circ}C; \; SQW$	-	18	Α
I _{FSM}	non-repetitive peak	$t_p = 10 \text{ ms}; T_{j(init)} = 25 \text{ °C}; SIN; Fig. 3$	-	91	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; Fig. 3	-	100	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

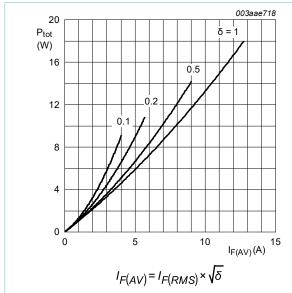


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

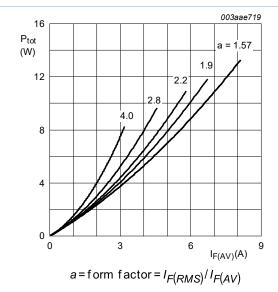
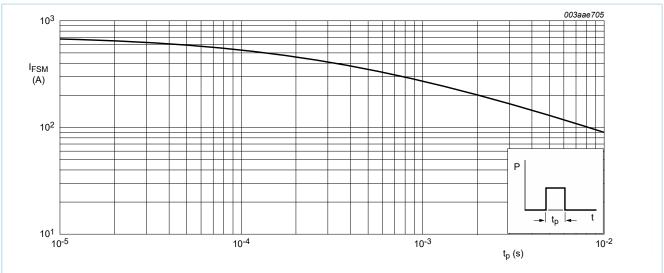


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4		-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	[1]	-	50	-	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

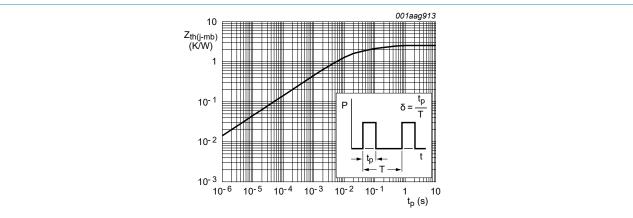
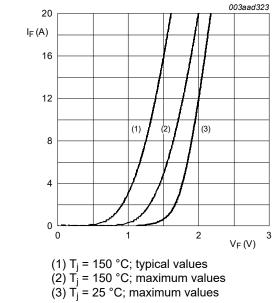


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.25	1.7	V
I _R	reverse current	V _R = 600 V; T _j = 100 °C	-	-	1.5	mA
		V _R = 600 V; T _j = 25 °C	-	-	50	μΑ
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 6}}{}$	-	17.5	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	1.5	-	Α
Q _r	recovered charge		-	13	-	nC
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; Fig. 7	-	3.2	-	V





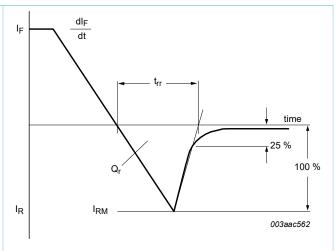
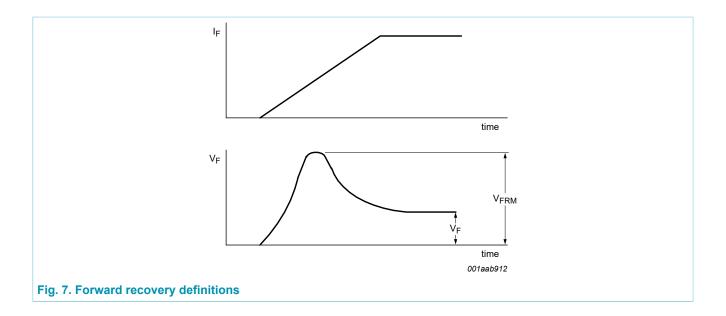


Fig. 6. Reverse recovery definitions; ramp recovery

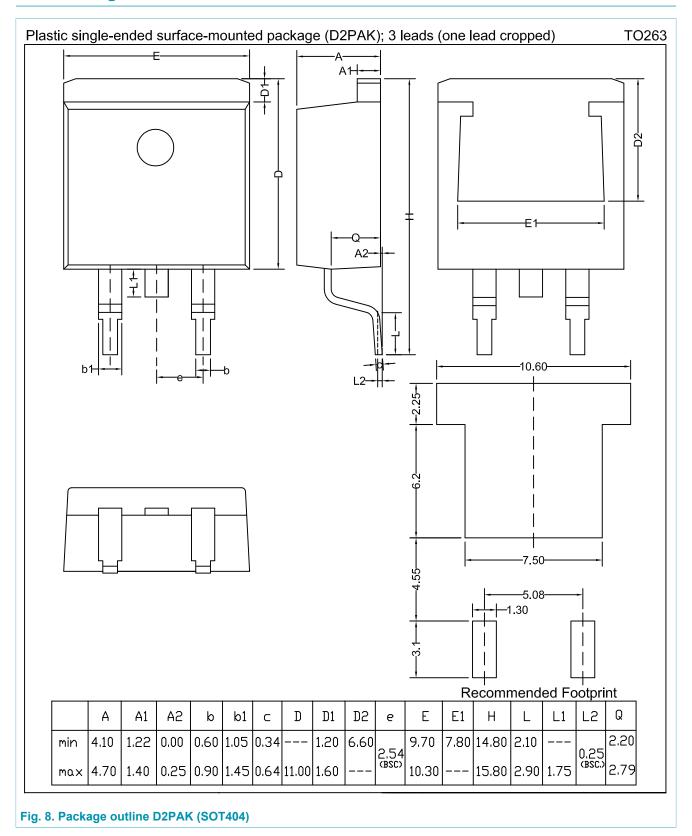
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10. Package outline



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11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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